

Low threshold operation of Distributed Reflector (DR) Laser with Quantum Wire Structures

Author: Mahjabin Mobarak

Department of Applied physics and Electronics and Communication Engineering, University of Dhaka
Tel: 880-01710936596 E-mail: ahmedmahjabin@gmail.com

Abstract

In this study Distributed Reflector (DR) laser consisting of a DFB laser with high reflection DBR at the rear end is studied by considering wirelike active region. Minimum threshold current of GaInAsP/InP laser has been analyzed. Lowest threshold of 0.305 mA has been observed is the DR laser with Double Quantum wire stack, 240 μ m cavity length of the active section, 90nm wire width and 2 μ m strip width. The proposed structure also provides very high differential quantum efficiency of about 63%.

Key word-Distributed reflector laser, Threshold Current, Quantum wire

1. INTRODUCTION

Distributed reflector Laser with DFB section is widely used in optical communication. To improve the performance the DR laser should have lower threshold current. Buried heterostructure lasers made from GaAs with wide stripe widths with a minimum threshold of 1.0mA has been reported. [1] A high differential quantum efficiency of about 50% from the front facet and low threshold current operation have been achieved by modifying the doping profile in 1.55- μ m distributed reflector lasers, waveguide loss Injection currents of 4.2 and 3.6 mA were obtained to achieve a 1-mW output power for lasers with uniform and phase-shifted grating structures, respectively.[2] A threshold current as low as 1.5 mA has been achieved for a distributed reflector (DR) laser consisting of an active DFB section and a passive DBR section by modulating widths of wirelike active regions.[3]

Fig. 1 shows the illustration and the grating structure of a DR laser, where L_a , Λ_a , and W_a denote the section length, the grating pitch, and the width of the wirelike active regions, respectively, and L_p , Λ_p , and W_p denote those of the passive sections. This laser has an active section with a DFB grating (left-hand side) and a passive section with a Q-wire DBR (right-hand side).

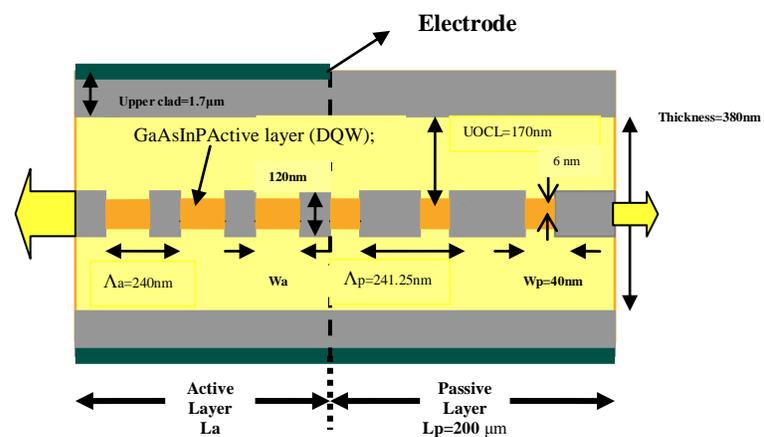


Fig 1 Schematic structure of DR laser (Single Quantum Wire)

In this structure the thickness of upper cladding layer is 1.7 μ m, lower cladding layer is also 1.7 μ m. Optical confinement layer (OCL) is 170nm on both sides. Thickness of a single wire is 6nm and thickness of the barrier is 9nm. L_p is 200 μ m, W_p is 40 nm, Λ_p is 241.25nm. L_a and W_a are different for different conditions. Λ_a is 240nm. Thickness of the active layer is different for different number of quantum wire stacked.

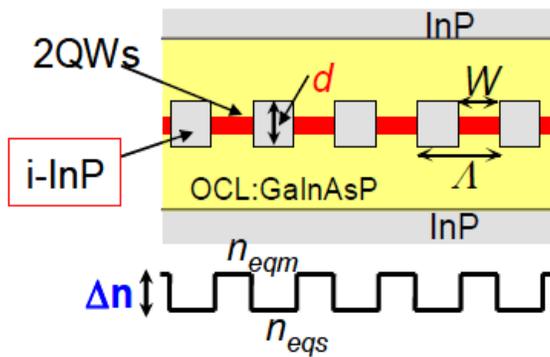


Figure 2: Refractive index profile

Figure 2 shows the refractive index profile of the active region where the equivalent refractive indices of gain and non-gain regions are denoted as n_{eqm} and n_{eqs} , respectively. The difference of these two equivalent refractive indices has been denoted as Δn as mentioned earlier. For a wire like DFB region with a wire width ratio (W/Λ) of 0.5 and $\Delta n=0.03$ ($n_{eqm}=3.21$, $n_{eqs}=3.18$), the maximum value of the index coupling coefficient becomes approximately 400 cm^{-1} . However, as the number of Quantum wire increased the depth of the groove is also increased. For SQW depth of the groove is 104nm, for DQW it is 120 nm, for 5QW it is 164 nm and for 10 QW it is 240 nm. The equivalent refractive index (n_{eqs}) of the etched region is decreased due to increased volume of InP, while the refractive index of the gain region (n_{eqm}) remains (approximately) the same; therefore, net Δn value is enhanced. In our study we calculate refractive index (n_{eqs}) of the etched region and gain region (n_{eqm}) using C programs. For single Quantum wire $n_{eqm}=3.23065$, $n_{eqs}=3.20136$ for double Quantum wire $n_{eqm}=3.2356$, $n_{eqs}=3.201356$ for 5 Quantum wire $n_{eqm}=3.25$, $n_{eqs}=3.1989$ for 10 Quantum wire $n_{eqm}=3.272$, $n_{eqs}=3.1955$.

2. Static characteristics of DR Laser

In this study C++ program is used to calculate the threshold current I_{th} and differential quantum efficiency η_d of DR laser.

In this paper we study on the dependence of threshold current on cavity length (CL) for different wire width of the active region. For different number of quantum wire it is shown in the following figures. It is found that I_{th} is very high for lower cavity length. It reduces as the cavity length increases and it reaches lowest value at certain cavity length. After that it begins to increase slowly.

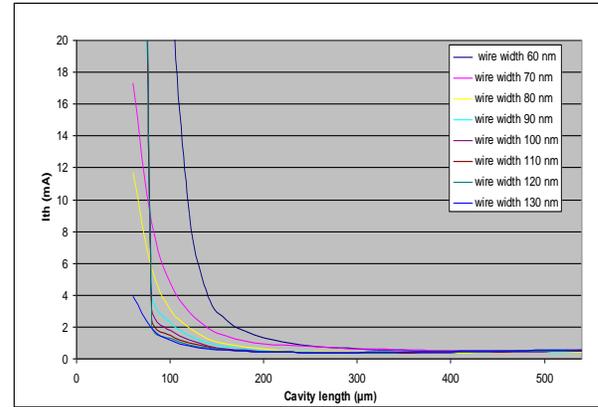


Fig 3 Dependence of threshold current on cavity length for Single Quantum wire.

From fig 3 it is shown that for Single Quantum Wire (SQW) at lower cavity length I_{th} is very high. For 60nm wire width it is 172mA (not shown in fig 3) then it reduce to minimum at $460\mu\text{m}$ cavity length to 0.4814mA. Similarly, the lowest threshold currents are obtained at different cavity length for different wire width. From all the data it is seen that minimum threshold current obtained at 100nm wire width which is 0.373mA where the cavity length is $300\mu\text{m}$.

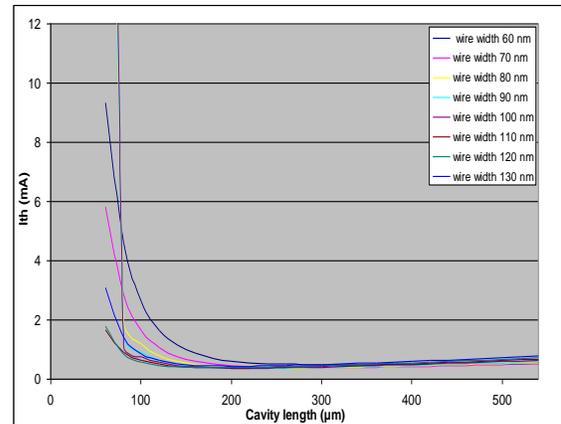


Fig 4 Dependence of threshold current on cavity length for Double Quantum wire.

For Double Quantum wire (DQW) I_{th} at lower cavity length is not that high as SQW. For 60nm wire length it is 9.33mA. But at 80nm, 90nm and 100nm wire width it is at higher side i.e. 39.8mA, 43mA and 48mA respectively (not shown in fig). From the entire wire width lowest threshold current is achieved at 90nm where I_{th} is 0.305mA where cavity length is $240\mu\text{m}$. (shown in fig 4)

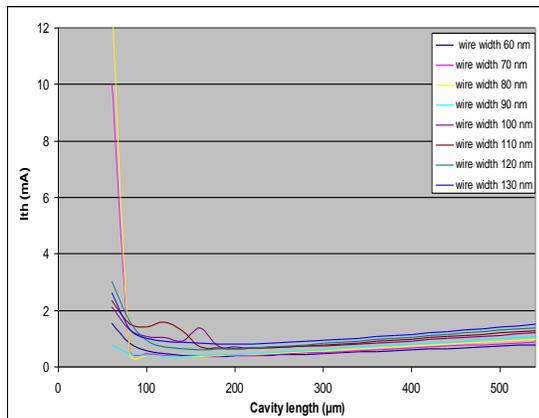


Fig 5 Dependence of threshold current on cavity length for 5 Quantum wire.

For 5 Quantum Well (5QW) I_{th} at lower cavity length (CL) is less than DQW. Here higher I_{th} are obtain at 70nm and 80nm wire width. Minimum I_{th} is obtained at 80nm wire width which is 0.371mA where the cavity length is 140 μm (as shown in fig 5.).

Figure 6 provides the dependence of threshold current on CL for 10 Quantum wire.

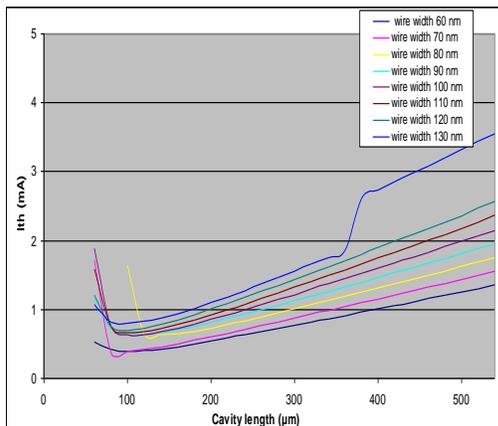


Fig 6 Dependence of threshold current on cavity length for 10 Quantum wire

For 10 Quantum Wire (10QW) I_{th} at lower cavity length (CL) is less than 5QW. So, in this section, it is seen that as the number of QW increases I_{th} at lower cavity length decreases. Here the minimum threshold current obtained at 70nm wire width where the CL is 80 μm and I_{th} is 0.381mA.

Conclusion:

After all these analysis it is found that lowest threshold current is obtained for single quantum well at 100nm wire width which is 0.373mA where the cavity length is 300 μm . For double quantum wire structure it is 0.305mA at 90nm wire width and 240 μm cavity length. For 5 QW minimum I_{th} is obtained at 80nm wire width which is 0.371mA where the cavity length is 140 μm and for 10 QW minimum

threshold current obtained at 70nm wire width where the CL is 80 μm and I_{th} is 0.381mA. It is observed that as the number of well increases required cavity length and wire width decreases for minimum threshold current. But confining to such a short length is very difficult. So we prefer double quantum wire structure at 90nm wire width with cavity length 240 μm where minimum threshold current is 0.305mA.

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